

L Number	Hits	Search Text	DB	Time stamp
1	1000	(physical and chemical) same etching same	USPAT;	2002/08/22 15:11
		plasma	US-PGPUB	
2	534	((physical and chemical) same etching same	USPAT;	2002/08/22 14:51
		plasma) and (nitrogen or argon or helium )	US-PGPUB	
3	328	(((physical and chemical) same etching	USPAT;	2002/08/22 15:11
		same plasma) and (nitrogen or argon or	US-PGPUB	
		helium )) and (trench or hole or opening		
		or recess)		( ( 1
4	177	((((physical and chemical) same etching	USPAT;	2002/08/22 14:52
		same plasma) and (nitrogen or argon or	US-PGPUB	
		helium )) and (trench or hole or opening or recess)) and (organic or polymer)		
5	177	(((((physical and chemical) same etching	USPAT;	2002/08/22 14:52
	1,,	same plasma) and (nitrogen or argon or	US-PGPUB	2002,00,22 132
		helium )) and (trench or hole or opening		
		or recess)) and (organic or polymer)) and		
		(cleaning or removing or etching)		
6	173	((((((physical and chemical) same etching	USPAT;	2002/08/22 14:53
		same plasma) and (nitrogen or argon or	US-PGPUB	
		helium )) and (trench or hole or opening		
		or recess)) and (organic or polymer)) and		
1		(cleaning or removing or etching)) and		
		@ad<=20010828		2000/00/00 15 11
7	98	(physical and chemical) same etching same	EPO; JPO;	2002/08/22 15:11
		plasma	DERWENT;	
8	16	((physical and chemical) same etching same	EPO; JPO;	2002/08/22 15:11
"	10	plasma) and (trench or hole or opening or	DERWENT;	2002/00/22 13:11
			1	
		recess)	IBM_TDB	

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	υ	1 [1 ]	Document :	[D	Issue Date	Pages
1			US 20020106 A1	845	20020808	14
2			US 20020073 A1	922	20020620	80
3		⊠	US 20020072 A1	223	20020613	22
4		×	US 20020022 A1	342	20020221	17
5		⊠	US 20020006 A1	674	20020117	21
6		⊠	US 20010055 A1	852	20011227	44
7		⊠	US 20010049 A1	150	20011206	42
8		⊠	US 20010046 A1	781	20011129	31
9		⊠	US 20010046 A1	780	20011129	26
10		×	US 20010030 A1	169	20011018	15
11		×	US 6432835	В1	20020813	59
12		⊠	US 6331380	В1	20011218	21
13		⊠	us 6307213	в1	20011023	9

	Title	Current OR	Current XRef
1	SURFACES OF A TRENCH	438/172	
2	CHAMBER LINER FOR HIGH TEMPERATURE PROCESSING CHAMBER	118/715	
3	Method of enhancing adhesion of a conductive barrier layer to an underlying conductive plug and contact for ferroelectric applications	438/629	
4	Method and device for producing a metal/metal contact in a multilayer metallization of an integrated circuit	438/453	
5	Hydrogen-free contact etch for ferroelectric capacitor formation	438/3	438/239; 438/256; 438/597
6	Integrated circuit and method	438/396	
7	Method for etching organic film, method for fabricating semiconductor device and pattern formation method	438/8	
8	Method for etching organic film, method for fabricating semiconductor device and pattern formation method	438/725	438/780
9	Method for etching organic film, method for fabricating semiconductor device and pattern formation method	438/712	
10	Method of etching organic film and method of producing element	216/17	216/41; 216/66
11	Process for fabricating an integrated circuit device having a capacitor with an electrode formed at a high aspect ratio	438/720	438/253; 438/396; 438/722
12	Method of pattern etching a low K dielectric layer	430./318	430/311; 430/313
13	Method for making a fuse structure for improved repaired yields on semiconductor memory devices	257/50	257/529; 257/530

	Retrieval Classif	Inventor	s	С	P	2	3	4	5
1		CHAO, JOHN et al.	$\boxtimes$						
2		FRANKEL, JONATHAN et al.	⊠						
3		Gilbert, Stephen R. et al.	⊠						
4		Schneegans, Manfred et al.	⊠						
5		Ma, Shawming et al.	×						
6		Moise, Theodore S. et al.	⊠						
7		Nakagawa, Hideo et al.	×						
8		Nakagawa, Hideo	×						
9		Nakagawa, Hideo	⊠						
10		Kitagawa, Hideo et al.	Ø						
11		Yunogami, Takashi et al.	Ø						
12		Ye, Yan et al.	Ø						
13		Huang, Kuo Ching et al.	×						

		mage Doc. Displayed	PT
1	US	20020106845	
2	US	20020073922	
3	US	20020072223	
4	US	20020022342	
5	US	20020006674	
6	US	20010055852	
7	US	20010049150	
8	US	20010046781	
9	US	20010046780	
10	US	20010030169	
11	US	6432835	
12	US	6331380	
13	US	6307213	

	ט	1 [1 ]	Do	ocument 1	.D	Issue	Date	Pages
14			US	6296777	B1	200110	02	8
15		⊠	US	6287961	в1	200109	11	19
16		⊠	US	6217786	в1	200104	17	10
17		Ø	US	6211035	В1	200104	03	42
18		Ø	US	6180533	В1	200101	30	22
19		⊠	US	6121073	A	200009	19	10
20		⊠	US	6103456	A	200008	315	13
21		⊠	US	6080529	А	200006	527	21
22		Ø	US	6004884	Α	199912	221	13
23		⊠	US	6004883	Α	199912	221	13
24		⊠	US	5980768	A	199911	109	12

	Title	Current OR	Current XRef
14	Structuring process	216/40	216/47; 216/49; 216/51; 216/67; 216/72; 216/76; 216/77; 216/78; 216/79
15	Dual damascene patterned conductor layer formation method without etch stop layer	438/638	438/637; 438/783; 438/924
16	Mechanism for bow reduction and critical dimension control in etching silicon dioxide using hydrogen-containing additive gases in fluorocarbon gas chemistry	216/79	438/710
17	Integrated circuit and method	438/396	
18	Method for etching a trench having rounded top corners in a silicon substrate	438/714	438/719; 438/724; 438/739
19	Method for making a fuse structure for improved repaired yields on semiconductor memory devices	438/132	438/601; 438/648; 438/662; 438/685
20	Prevention of photoresist poisoning from dielectric antireflective coating in semiconductor fabrication	430/317	430/314; 430/316
21	Method of etching patterned layers useful as masking during subsequent etching or for damascene structures	430/318	430/311; 430/313
22	Methods and apparatus for etching semiconductor wafers	438/714	216/72; 438/738; 438/742; 438/952
23	Dual damascene patterned conductor layer formation method without etch stop layer	438/706	438/711; 438/723
24	Methods and apparatus for removing photoresist mask defects in a plasma reactor	216/67	216/72; 438/710

	Retrieval Classif	Inventor	s	С	P	2	3	4	5
14		Engelhardt, Manfred et al.	⊠						
15		Liu, Chung-Shi et al.	⊠						
16		Hills, Graham et al.	⊠						
17		Moise, Theodore S. et al.	☒						
18		Jain, Alok et al.	×						
19		Huang, Kuo Ching et al.	⊠						
20		Tobben, Dirk et al.	Ø						
21		Ye, Yan et al.	⊠						
22		Abraham, Susan C.	⊠						
23		Yu, Chen-Hua Douglas et al.	⊠						
24		Abraham, Susan C.	⊠						

	I	mage Doc. Displayed	PT
14	US	6296777	
15	US	6287961	
16	US	6217786	
17	US	6211035	
18	US	6180533	
19	US	6121073	
20	US	6103456	
21	US	6080529	
22	US	6004884	
23	US	6004883	
24	US	5980768	

	ט	1 [1 ]	D	ocument	ID	Issue Date	Pages
25		⊠	US	5976986	А	19991102	11
26		⊠	US	5925577	А	19990720	13
27		×	US	5895239	A	19990420	21
28		×	US	5893734	A	19990413	19
29		×	US	5851302	A	19981222	8
30		☒	US	5843848	Α	19981201	16
31		Ø	US	5772906	Α	19980630	15
32		Ø	US	5670421	A	19970923	31
33		⊠	US	5545290	А	19960813	8
34		Ø	US	5213659	A	19930525	6
35		☒	US	5157000	А	19921020	6

	Title	Current OR	Current XRef
25	Low pressure and low power C1.sub.2 /HC1 process for sub-micron metal etching	438/714	204/192.35; 438/696; 438/720
26	Method for forming via contact hole in a semiconductor device	438/725	134/1.1; 134/1.2; 134/1.3; 216/17; 438/637; 438/639; 438/669; 438/704; 438/720; 438/963
27	Method for fabricating dynamic random access memory (DRAM) by simultaneous formation of tungsten bit lines and tungsten landing plug contacts	438/239	438/254
28	Method for fabricating capacitor-under-bit line (CUB) dynamic random access memory (DRAM) using tungsten landing plug contacts	438/239	438/254
29	Method for dry etching sidewall polymer	134/1.2	438/696; 438/723; 438/725; 438/734; 438/740
30	Method of plasma etching	438/738	216/77; 438/721; 438/742
31	Mechanism for uniform etching by minimizing effects of etch rate loading		216/67; 438/714; 438/740
32	Process for forming multilayer wiring	438/641	438/675; 438/677
33	Etching method	438/695	216/37; 216/58; 216/64; 438/696
34	Combination usage of noble gases for dry etching semiconductor wafers	216/48	216/66 <b>;</b> 216/79
35	Method for dry etching openings in integrated circuit layers	438/704	148/DIG.51; 427/576

	Retrieval Classif	Inventor	s	С	P	2	3	4	5
25		Naeem, Munir D. et al.	×						
26		Solis, Ramiro	⊠						
27		Jeng, Erik S. et al.	⊠						
28		Jeng, Erik S. et al.	⊠						
29		Solis, Ramiro	⊠						
30		Yanagawa, Shusaku	☒						
31		Abraham, Susan C.	×						
32		Nishitani, Eisuke et al.	Ø						
33		Douglas, Monte A.	Ø						
34		Blalock, Guy T. et al.	☒						
35		Elkind, Jerome L. et al.	⊠						

	]	mage Doc. Displayed	PT
25	US	5976986	
26	US	5925577	
27	US	5895239	
28	US	5893734	
29	US	5851302	
30	US	5843848	
31	US	5772906	
32	US	5670421	
33	US	5545290	
34	US	5213659	
35	US	5157000	

	ŭ	1 [1 ]	Document	ID	Issue Date	Pages
36		×	US 4529860	А	19850716	8
37		⊠	US 4376672	Α	19830315	15

	Title	Curr nt OR	Current XRef
36	Plasma etching of organic materials	219/121.41	216/58; 216/67; 219/121.42; 219/121.43; 430/313; 430/323; 430/330
37	Materials and methods for plasma etching of oxides and nitrides of silicon	438/713	148/DIG.131; 204/192.32; 204/298.31; 252/79.1; 430/313; 430/317; 438/723; 438/724

	Retrieval Classif	Inventor	s	C	P	2	3	4	5
36		Robb, Francine Y.							
37		Wang, David N. et al.							

	Image Doc. Displayed	PT
36	US 4529860	
37	US 4376672	